

# SMP1302-085LF: Surface Mount PIN Diode for High Power Switch Applications

## Applications

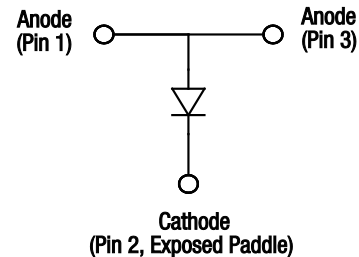
- Low loss, high power switches
- Low distortion attenuators

## Features

- Low-thermal resistance: 22 °C/W
- Suitable for 140 W Continuous Wave T/R switches
- Low capacitance: 0.3 pF
- Low distortion performance
- QFN (3-pin, 2 x 2 mm) package (MSL1, 260 °C per JEDEC J-STD-020)



Skyworks Green™ products are compliant with all applicable legislation and are halogen-free. For additional information, refer to *Skyworks Definition of Green™*, document number SQ04-0074.



**Figure 1. SMP1302-085LF Block Diagram**

## Description

The SMP1302-085LF is a surface mountable, low capacitance silicon PIN diode designed as a shunt connected PIN diode for high power, high volume switch and attenuator applications from 10 MHz to beyond 6 GHz.

Maximum resistance at 100 mA is 1.5 Ω and maximum capacitance at 30 V is 0.35 pF. The combination of low junction capacitance, low parasitic inductance, low thermal resistance, and nominal 50 μm I-region width, makes the SMP1302-085LF useful in large signal switches and attenuator applications.

The device has a 2.8 W dissipation power rating, making it capable of handling more than 140 W Continuous Wave (CW) and 500 W peak (1 μs pulse, 1 percent duty cycle) in a shunt-connected transmit/receive (T/R) switch.

Design information for high power switches may be found in the Skyworks Application Note, *Design With PIN Diodes* (document number 200312).

A block diagram of the SMP1302-085LF is shown in Figure 1.

**Table 1. SMP1302-085LF Absolute Maximum Ratings**

Parameter	Symbol	Minimum	Maximum	Units
Reverse voltage	$V_R$		200	V
Forward current @ 25 °C	$I_F$		200	mA
CW power dissipation @ 85 °C	$P_D$		2.8	W
1 $\mu$ s pulse power dissipation			30	W
Storage temperature	$T_{STG}$	-65	+200	°C
Operating temperature	$T_A$	-40	+150	°C
Electrostatic Discharge:	ESD			
Charged Device Model (CDM), Class 4			1100	V
Human Body Model (HBM), Class 1C			1000	V
Machine Model (MM), Class C			400	V

**Note:** Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.

**CAUTION:** Although this device is designed to be as robust as possible, Electrostatic Discharge (ESD) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions should be used at all times.

**Table 2. SMP1302-085LF Electrical Specifications (Note 1)**  
( $T_A = +25$  °C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typical	Max	Units
Reverse current	$I_R$	$V_R = 200$ V			10	$\mu$ A
Capacitance	$C_T$	$f = 1$ MHz, $V_R = 30$ V			0.35	pF
Resistance	$R_S$	$f = 100$ MHz $I_F = 10$ mA $I_F = 100$ mA		1.0	3 1.5	$\Omega$ $\Omega$
Forward voltage	$V_F$	$I_F = 10$ mA		0.8		V
Carrier lifetime	$T_L$	$I_F = 10$ mA		700		ns
I region width	$W$			50		$\mu$ m
CW thermal resistance	$\theta_{JC}$	Junction to case		22		°C/W
Pulse thermal resistance	$\theta_P$	Single 1 $\mu$ s pulse. Junction to external surface.		3.5		°C/W

**Note 1:** Performance is guaranteed only under the conditions listed in this Table.

**Electrical and Mechanical Specifications**

The absolute maximum ratings of the SMP1302-085LF are provided in Table 1. Electrical specifications are provided in Table 2.

Typical performance characteristics of the SMP1302-085LF are illustrated in Figures 2 to 4.

### Typical Performance Characteristics

(T<sub>A</sub> = 25 °C, Unless Otherwise Noted)

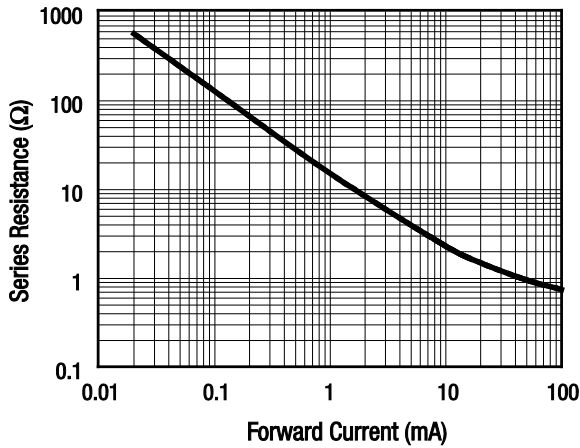


Figure 2. Series Resistance vs Current @ 100 MHz

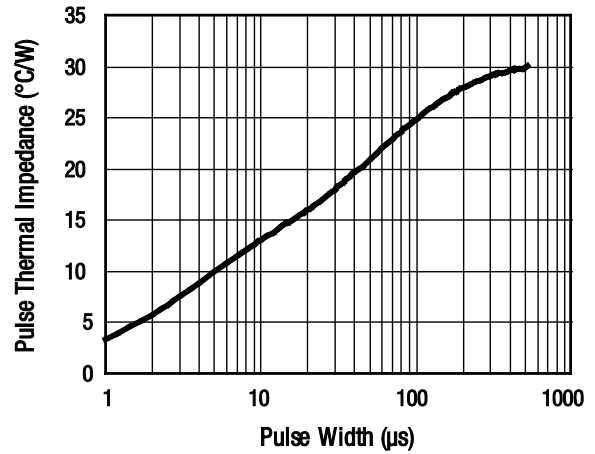


Figure 3. Typical Pulse Thermal Impedance

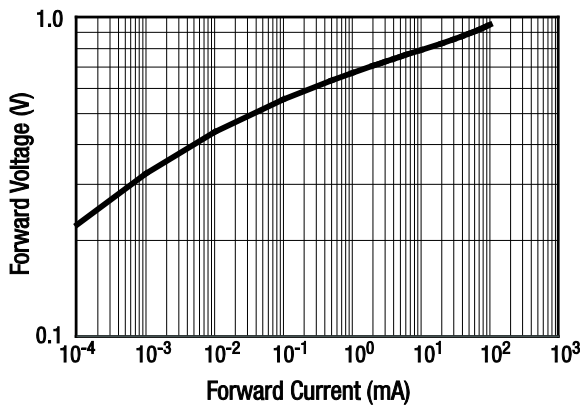


Figure 4. Forward Voltage vs Forward Current

### High Power Switch Design Application

The SMP1302-085LF PIN diode is designed for shunt applications such as reflective switches or shunt-diode attenuator circuits. Compared to other surface mount packages, the design of the QFN package produces lower thermal resistance and also reduces the effects of the parasitic inductance of the anode bond wires.

A cross-sectional view of the SMP1302-085LF PIN diode is shown in Figure 5. The cathode of the die is soldered directly to the top of the exposed paddle. This paddle is composed of copper, so its thermal resistance is very low.

The copper ground paddle minimizes the total thermal resistance between the I layer, which is the location where most heat is generated under normal operation, and the surface to which the package is mounted. Minimal thermal resistance between the I layer and the external environment minimizes junction temperature.

The electrically equivalent circuit of the SMP1302-085LF PIN diode is shown in Figure 6. The inductances of pins 1 and 2, as well as the inductances of the bond wires are in series with the input and output transmission lines of the external circuit rather than the portion of the circuit that contains the shunt PIN diode.

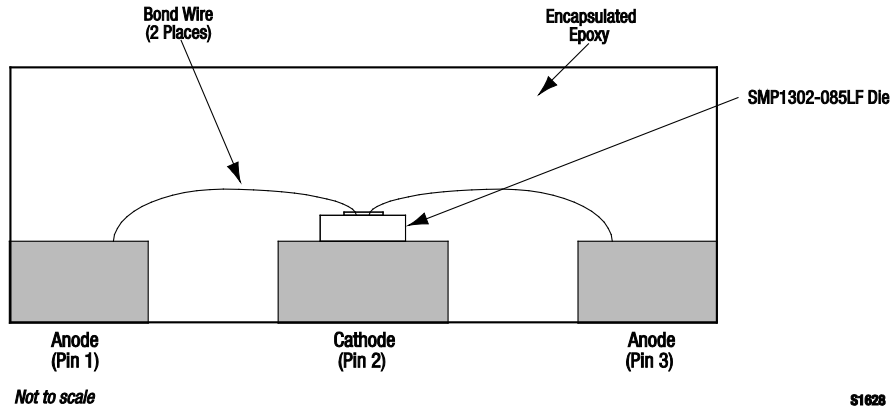


Figure 5. Cross-Sectional View of the SMP1302-085LF

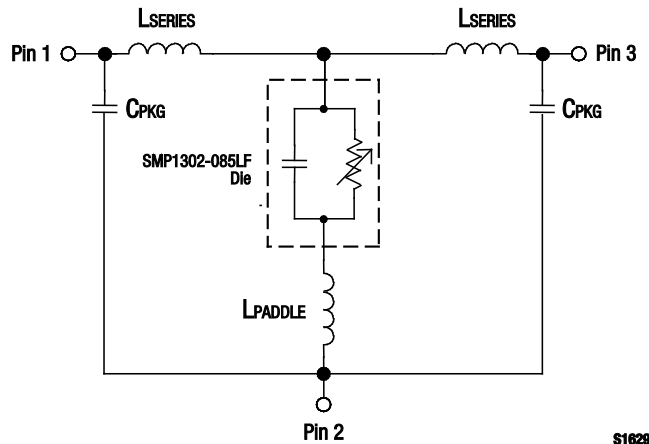


Figure 6. SMP1302-085LF Electrically Equivalent Circuit

The effects of these parasitic series inductances are negligible, since they add a very small insertion loss to the shunt PIN but have no effect on the isolation that the diode produces when it is forward biased.

A cross section of the suggested printed circuit board design is shown in Figure 7. The via shown in this view is critical, both for electrical performance and for thermal performance. It is recommended that several vias should be placed under the entire footprint of the exposed paddle (pin 2) to minimize both electrical inductance to the system ground and thermal resistance to the system heat sink.

### A Transmit/Receive Switch Design

A T/R switch incorporating a pair of SMP1302-085LF PIN diodes and covering 2.0155 GHz to 2.0195 GHz has been designed and tested. This circuit is shown in Figure 8. The switch operated safely at a transmitter input power of +41 dBm CW (12.6 W) with

low insertion loss (0.42 dB) and high receiver isolation (37 dB). The input 1 dB compression point is higher than +50 dBm. In the receive state, the switch produced 0.45 dB insertion loss and 37.8 dB transmitter isolation.

The circuit is based on a quarter wave design using two shunt-connected SMP1302-085LF diodes. In the transmit state, Bias 1 is set at 0 mA and Bias 2 is set at 50 mA. Under these conditions, D1 is held out of conduction so its impedance remains high and a very small insertion loss is introduced to the path between the transmitter port and the antenna port.

D2 is forced into conduction, which lowers its series resistance towards its minimum value of <math><1 \Omega</math>. In this state, energy that propagates from either the transmitter port or the antenna port is reflected, which isolates the receiver port from the remainder of the circuit.

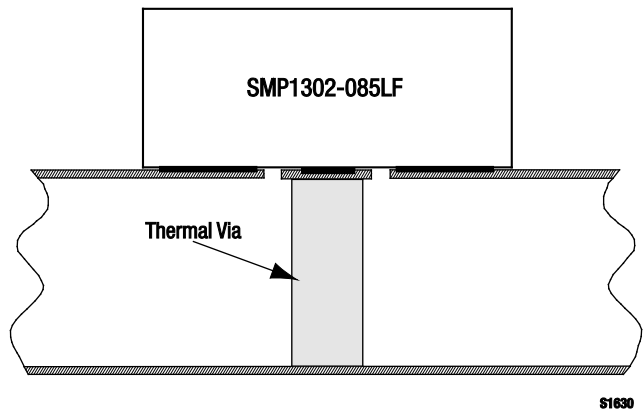


Figure 7. Cross-Sectional View of Suggested Printed Circuit Board

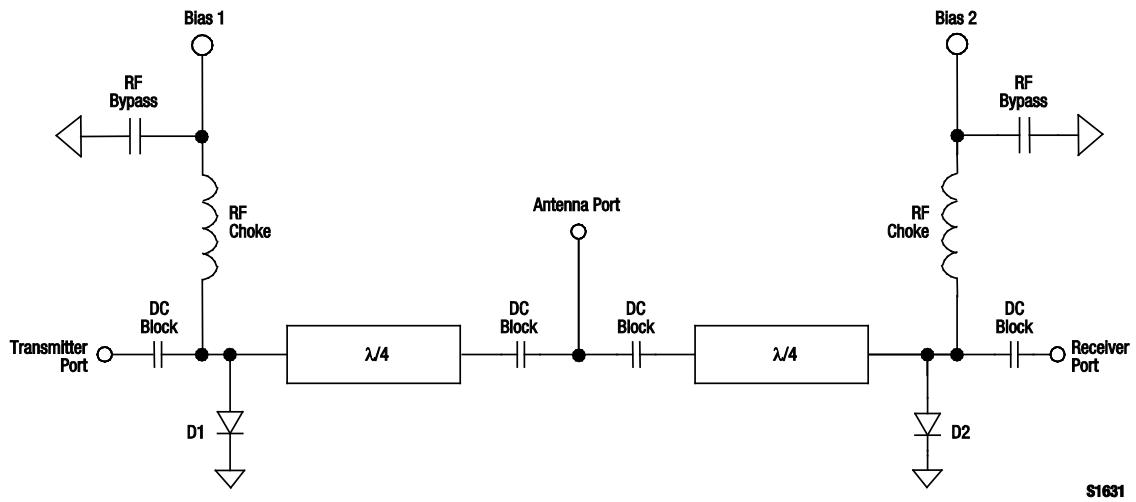


Figure 8. T/R Switch Design: 2.0155 GHz to 2.0195 GHz

**Table 3. Measured T/R Switch Performance**

Parameter	Symbol	Conditions	Value
Frequency			2.010 to 2.025 GHz
Insertion loss (transmit port to antenna)		Bias 1 = 0 mA, Bias 2 = 50 mA	0.42 dB
Insertion loss (antenna to receive port)		Bias 1 = 50 mA, Bias 2 = 0 mA	0.45 dB
Isolation (receive port to transmit port)		Bias 1 = 0 mA, Bias 2 = 50 mA	37 dB
Isolation (transmit port to receive port)		Bias 1 = 50 mA, Bias 2 = 0 mA	37.8 dB
0.1 dB Input Compression Point	IPO.1dB	Bias 1 = 0 mA, Bias 2 = 50 mA, pulse width = 8 μs, duty cycle = 0.5%	+46 dBm
1 dB Input Compression Point	IP1dB	Bias 1 = 0 mA, Bias 2 = 50 mA, pulse width = 8 μs, duty cycle = 0.5%	>+50 dBm
3 <sup>rd</sup> Order Input Intercept Point	IIP3	f1 = 2.0155 GHz, f2= 2.0195 GHz	>+80 dBm
Maximum transmit CW input power		Bias 1 = 0 mA, Bias 2 = 50 mA	+41 dBm
Maximum pulsed transmit input power		Bias 1 = 0 mA, Bias 2 = 50 mA, pulse width = 8 μs, duty cycle = 0.5%	>+49.5 dBm
Switching speed	T <sub>sw</sub>	Transmit state to receive state, Bias 1 = 0/50 mA, Bias 2 = 50/0 mA	<0.85 μs
Transmit input return loss		Bias 1 = 0 mA, Bias 2 = 50 mA	27.8 dB
Receive input return loss		Bias 1 = 50 mA, Bias 2 = 0 mA	28.8 dB

The quarter wave line connected between D2 and the antenna port transforms the very low impedance of the diode to a very high impedance looking from the antenna port towards the receive port. This produces minimal insertion loss in the transmitter-to-antenna path.

In the receive state, Bias 1 is set at 50 mA and Bias 2 is set at 0 mA. The operation of the T/R switch in this state is the converse of the operation in the transmit state: the transmitter port is isolated from the antenna port and the antenna and receive ports are connected to each other using a low-insertion-loss path.

The measured performance of this circuit is summarized in Table 3.

**Package Dimensions**

The PCB layout footprint for the SMP1302-085LF is shown in Figure 9. Typical case markings are shown in Figure 10. Package dimensions for the 3-pin QFN are provided in Figure 11, and Figure 12 provides the tape and reel dimensions.

**Package and Handling Information**

Instructions on the shipping container label regarding exposure to moisture after the container seal is broken must be followed. Otherwise, problems related to moisture absorption may occur when the part is subjected to high temperature during solder assembly.

The SMP1302-085LF is rated to Moisture Sensitivity Level 1 (MSL1) at 260 °C. It can be used for lead or lead-free soldering. For additional information, refer to the Skyworks Application Note, *Solder Reflow Information*, document number 200164.

Care must be taken when attaching this product, whether it is done manually or in a production solder reflow environment. Production quantities of this product are shipped in a standard tape and reel format.

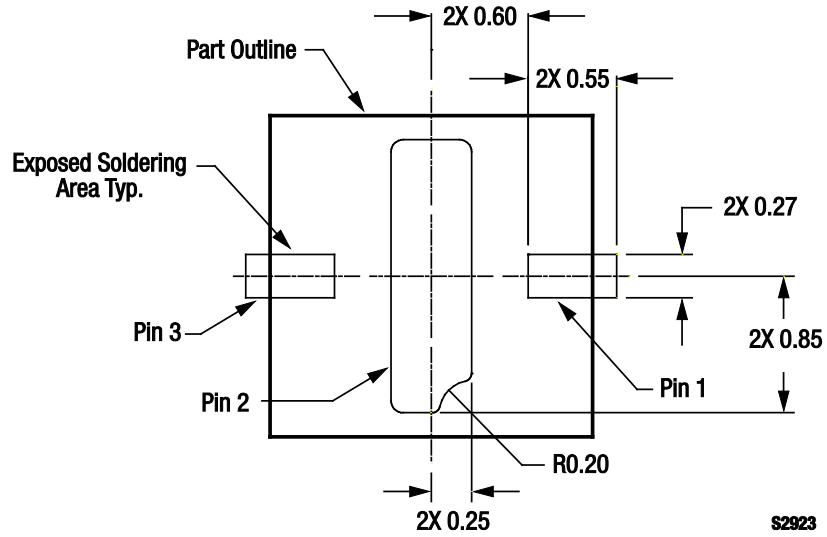


Figure 9. SMP1302-085LF PCB Layout Footprint

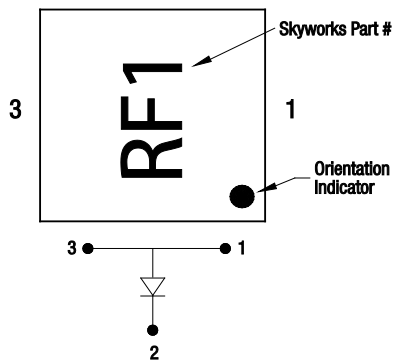
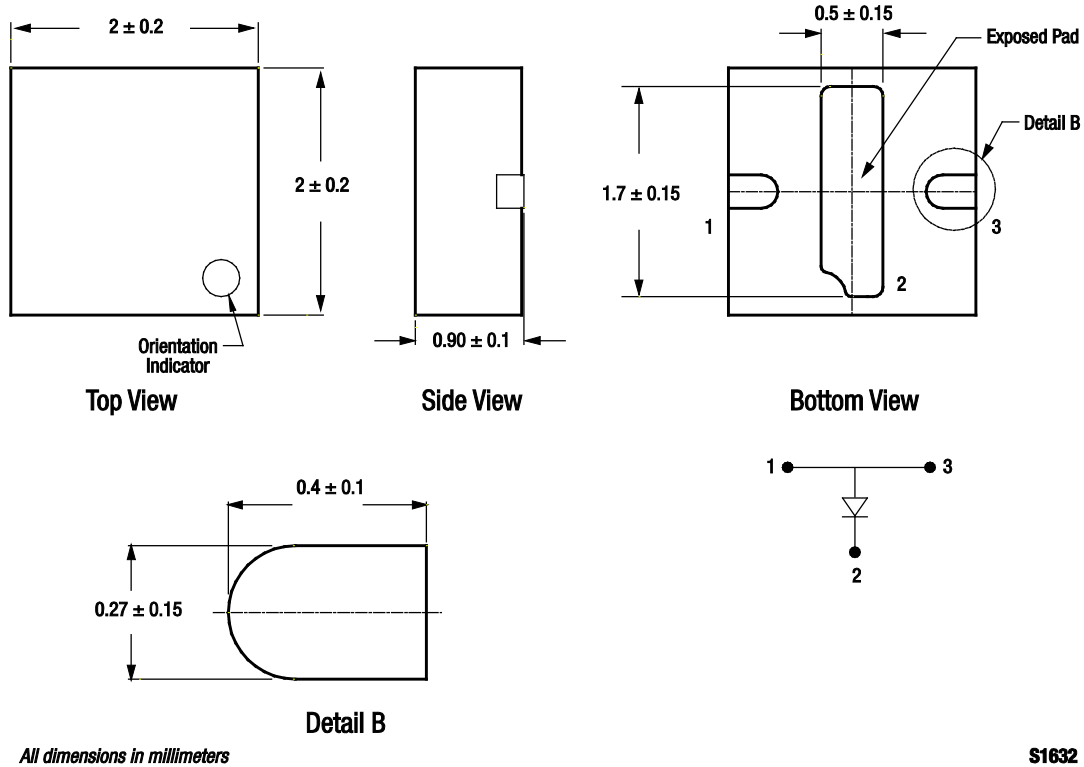
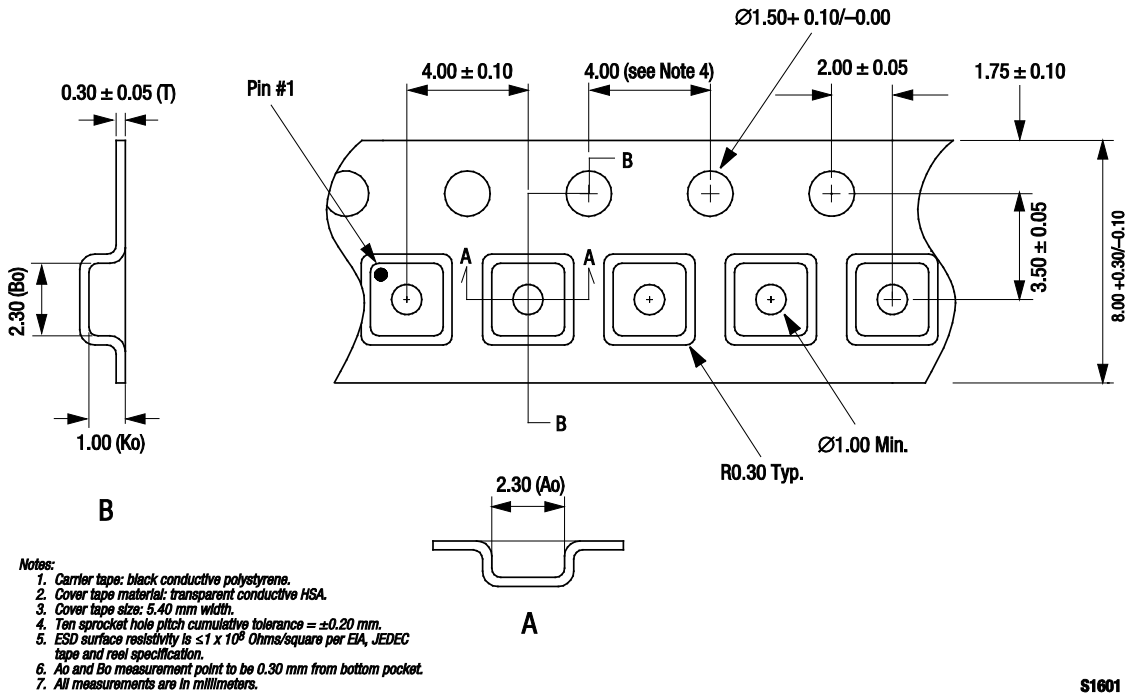


Figure 10. Typical Case Markings (Top View)



**Figure 11. SMP1302-085LF QFN Package Dimension Drawing**



**Figure 12. SMP1302-085LF Tape and Reel Dimensions**



**Ordering Information**

Model Name	Manufacturing Part Number
SMP1302-085LF Surface Mount PIN Diode	SMP1302-085LF

Copyright © 2009, 2010, 2011, 2012, 2013 Skyworks Solutions, Inc. All Rights Reserved.

Information in this document is provided in connection with Skyworks Solutions, Inc. (“Skyworks”) products or services. These materials, including the information contained herein, are provided by Skyworks as a service to its customers and may be used for informational purposes only by the customer. Skyworks assumes no responsibility for errors or omissions in these materials or the information contained herein. Skyworks may change its documentation, products, services, specifications or product descriptions at any time, without notice. Skyworks makes no commitment to update the materials or information and shall have no responsibility whatsoever for conflicts, incompatibilities, or other difficulties arising from any future changes.

No license, whether express, implied, by estoppel or otherwise, is granted to any intellectual property rights by this document. Skyworks assumes no liability for any materials, products or information provided hereunder, including the sale, distribution, reproduction or use of Skyworks products, information or materials, except as may be provided in Skyworks Terms and Conditions of Sale.

THE MATERIALS, PRODUCTS AND INFORMATION ARE PROVIDED “AS IS” WITHOUT WARRANTY OF ANY KIND, WHETHER EXPRESS, IMPLIED, STATUTORY, OR OTHERWISE, INCLUDING FITNESS FOR A PARTICULAR PURPOSE OR USE, MERCHANTABILITY, PERFORMANCE, QUALITY OR NON-INFRINGEMENT OF ANY INTELLECTUAL PROPERTY RIGHT; ALL SUCH WARRANTIES ARE HEREBY EXPRESSLY DISCLAIMED. SKYWORKS DOES NOT WARRANT THE ACCURACY OR COMPLETENESS OF THE INFORMATION, TEXT, GRAPHICS OR OTHER ITEMS CONTAINED WITHIN THESE MATERIALS. SKYWORKS SHALL NOT BE LIABLE FOR ANY DAMAGES, INCLUDING BUT NOT LIMITED TO ANY SPECIAL, INDIRECT, INCIDENTAL, STATUTORY, OR CONSEQUENTIAL DAMAGES, INCLUDING WITHOUT LIMITATION, LOST REVENUES OR LOST PROFITS THAT MAY RESULT FROM THE USE OF THE MATERIALS OR INFORMATION, WHETHER OR NOT THE RECIPIENT OF MATERIALS HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGE.

Skyworks products are not intended for use in medical, lifesaving or life-sustaining applications, or other equipment in which the failure of the Skyworks products could lead to personal injury, death, physical or environmental damage. Skyworks customers using or selling Skyworks products for use in such applications do so at their own risk and agree to fully indemnify Skyworks for any damages resulting from such improper use or sale.

Customers are responsible for their products and applications using Skyworks products, which may deviate from published specifications as a result of design defects, errors, or operation of products outside of published parameters or design specifications. Customers should include design and operating safeguards to minimize these and other risks. Skyworks assumes no liability for applications assistance, customer product design, or damage to any equipment resulting from the use of Skyworks products outside of stated published specifications or parameters.

Skyworks, the Skyworks symbol, and “Breakthrough Simplicity” are trademarks or registered trademarks of Skyworks Solutions, Inc., in the United States and other countries. Third-party brands and names are for identification purposes only, and are the property of their respective owners. Additional information, including relevant terms and conditions, posted at [www.skyworksinc.com](http://www.skyworksinc.com), are incorporated by reference.

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9